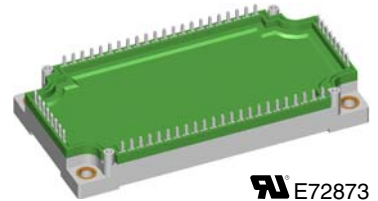
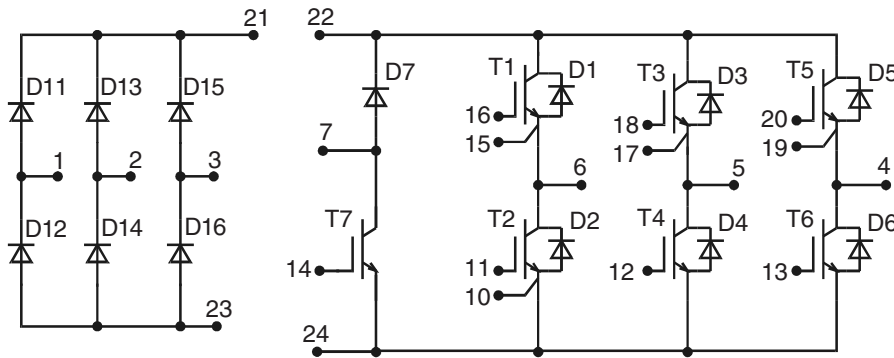
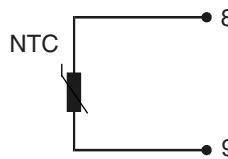


# Converter - Brake - Inverter Module (CBI3)


**IXYS E72873**

See outline drawing for pin arrangement

## Preliminary data



Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{FAVM} = 90 \text{ A}$	$I_{C25} = 50 \text{ A}$	$I_{C25} = 125 \text{ A}$
$I_{FSM} = 850 \text{ A}$	$V_{CE(sat)} = 1.9 \text{ V}$	$V_{CE(sat)} = 1.9 \text{ V}$

Input Rectifier D11 - D16		
Symbol	Conditions	Maximum Ratings
$V_{RRM}$		1600 V
$I_{FAV}$	$T_C = 80^\circ\text{C}$ ; sine 180°	65 A
$I_{DAVM}$	$T_C = 80^\circ\text{C}$ ; rectangular; $d = 1/3$ ; bridge	180 A
$I_{FSM}$	$T_{VJ} = 25^\circ\text{C}$ ; $t = 10 \text{ ms}$ ; sine 50 Hz	850 A
$P_{tot}$	$T_C = 25^\circ\text{C}$	170 W

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 100 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.3	1.5 V
$I_R$	$V_R = V_{RRM}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1	0.05 mA mA
$R_{thJC}$	(per diode)			0.73 K/W

## Application: AC motor drives with

- € Input from single or three phase grid
- € Three phase synchronous or asynchronous motor
- € electric braking operation

## Features

- € High level of integration - only one power semiconductor module required for the whole drive
- € NPT IGBT technology with low saturation voltage, low switching losses, high RBSOA and short circuit ruggedness
- € Epitaxial free wheeling diodes with Hiperfast and soft reverse recovery
- € Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- € Temperature sense included

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**Output Inverter T1 - T6**

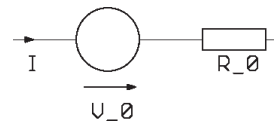
Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	125	A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	85	A
<b>RBSOA</b>	$V_{GE} = \pm 15\text{ V}$ ; $R_G = 2.2\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100\ \mu\text{H}$	$I_{CM} = 200$ $V_{CEK} \leq V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{CE} = V_{CES}$ ; $V_{GE} = \pm 15\text{ V}$ ; $R_G = 2.2\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	410	W

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 100\text{ A}$ ; $V_{GE} = 15\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9 2.2	2.5	V V
$V_{GE(th)}$	$I_C = 1.5\text{ mA}$ ; $V_{GE} = V_{CE}$	4.5	6.5	V
$I_{CES}$	$V_{CE} = V_{CES}$ ; $V_{GE} = 0\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.5	1.4	mA mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ ; $V_{GE} = \pm 20\text{ V}$		400	nA
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300\text{ V}$ ; $I_C = 100\text{ A}$ $V_{GE} = \pm 15\text{ V}$ ; $R_G = 2.2\ \Omega$		25	ns
			11	ns
			150	ns
			30	ns
			1.0	mJ
			2.9	mJ
$C_{ies}$	$V_{CE} = 25\text{ V}$ ; $V_{GE} = 0\text{ V}$ ; $f = 1\text{ MHz}$	4.3		nF
$Q_{Gon}$	$V_{CE} = 300\text{ V}$ ; $V_{GE} = 15\text{ V}$ ; $I_C = 125\text{ A}$	340		nC
$R_{thJC}$	(per IGBT)			0.3 K/W

**Output Inverter D1 - D6**

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^{\circ}\text{C}$	140	A
$I_{F80}$	$T_C = 80^{\circ}\text{C}$	85	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 100\text{ A}$ ; $V_{GE} = 0\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9 1.4	2.2	V V
$I_{RM}$ $t_{rr}$	$I_F = 60\text{ A}$ ; $di_F/dt = -500\text{ A}/\mu\text{s}$ ; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 300\text{ V}$ ; $V_{GE} = 0\text{ V}$	28		A
		100		ns
$R_{thJC}$	(per diode)			0.61 K/W

**Equivalent Circuits for Simulation**
**Conduction**

 IGBT (typ. at  $V_{GE} = 15\text{ V}$ ;  $T_J = 125^{\circ}\text{C}$ )  
T1-T6

$$V_0 = 1.05\text{ V}; R_0 = 11.5\text{ m}\Omega$$

T7

$$V_0 = 1.05\text{ V}; R_0 = 21.5\text{ m}\Omega$$

 Diode (typ. at  $T_J = 125^{\circ}\text{C}$ )

D1-D6

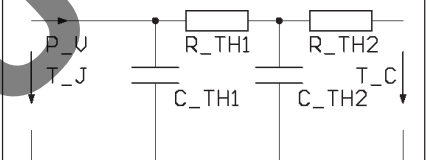
$$V_0 = 1.15\text{ V}; R_0 = 2.5\text{ m}\Omega$$

D7

$$V_0 = 1.15\text{ V}; R_0 = 12.5\text{ m}\Omega$$

D11-D16

$$V_0 = 0.85\text{ V}; R_0 = 4\text{ m}\Omega$$

**Thermal Response**


IGBT (typ.)

T1-T6

$$C_{th1} = 0.232\text{ J/K}; R_{th1} = 0.223\text{ K/W}$$

$$C_{th2} = 1.504\text{ J/K}; R_{th2} = 0.077\text{ K/W}$$

T7

$$C_{th1} = 0.123\text{ J/K}; R_{th1} = 0.419\text{ K/W}$$

$$C_{th2} = 0.944\text{ J/K}; R_{th2} = 0.131\text{ K/W}$$

Diode (typ.)

D1-D6

$$C_{th1} = 0.138\text{ J/K}; R_{th1} = 0.48\text{ K/W}$$

$$C_{th2} = 0.957\text{ J/K}; R_{th2} = 0.13\text{ K/W}$$

D7

$$C_{th1} = 0.038\text{ J/K}; R_{th1} = 1.74\text{ K/W}$$

$$C_{th2} = 0.435\text{ J/K}; R_{th2} = 0.36\text{ K/W}$$

D11-D16

$$C_{th1} = 0.112\text{ J/K}; R_{th1} = 0.568\text{ K/W}$$

$$C_{th2} = 0.745\text{ J/K}; R_{th2} = 0.162\text{ K/W}$$

**Brake Chopper T7**

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	75	A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	50	A
<b>RBSOA</b>	$V_{GE} = \pm 15\text{ V}$ ; $R_G = 22\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100\ \mu\text{H}$	$I_{CM} = 100$ $V_{CEK} \leq V_{CES}$	A
<b>t<sub>SC</sub></b> <b>(SCSOA)</b>	$V_{CE} = V_{CES}$ ; $V_{GE} = \pm 15\text{ V}$ ; $R_G = 22\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
<b>P<sub>tot</sub></b>	$T_C = 25^{\circ}\text{C}$	225	W

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 50\text{ A}$ ; $V_{GE} = 15\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.9	2.3 V
			2.1	V
$V_{GE(th)}$	$I_C = 1\text{ mA}$ ; $V_{GE} = V_{CE}$	4.5		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ ; $V_{GE} = 0\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.5	0.5 mA mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ ; $V_{GE} = \pm 20\text{ V}$			200 nA
$t_{d(on)}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300\text{ V}$ ; $I_C = 50\text{ A}$ $V_{GE} = \pm 15\text{ V}$ ; $R_G = 22\ \Omega$		50	ns
$t_r$			55	ns
$t_{d(off)}$			300	ns
$t_f$			30	ns
$E_{on}$			2.3	mJ
$E_{off}$			1.7	mJ
$C_{ies}$	$V_{CE} = 25\text{ V}$ ; $V_{GE} = 0\text{ V}$ ; $f = 1\text{ MHz}$		2.8	nF
$Q_{Gon}$	$V_{CE} = 300\text{ V}$ ; $V_{GE} = 15\text{ V}$ ; $I_C = 50\text{ A}$		120	nC
$R_{thJC}$				0.55 K/W

**Brake Chopper D7**

Symbol	Conditions	Maximum Ratings	
$V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	600	V
$I_{F25}$	$T_C = 25^{\circ}\text{C}$	35	A
$I_{F80}$	$T_C = 80^{\circ}\text{C}$	24	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 50\text{ A}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.2	2.5 V
			1.8	V
$I_R$	$V_R = V_{RRM}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	0.1 mA mA
$I_{RM}$	$I_F = 15\text{ A}$ ; $di_F/dt = -400\text{ A}/\mu\text{s}$ ; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 300\text{ V}$		13	A
$t_{rr}$			90	ns
$R_{thJC}$				2.1 K/W

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### Temperature Sensor NTC

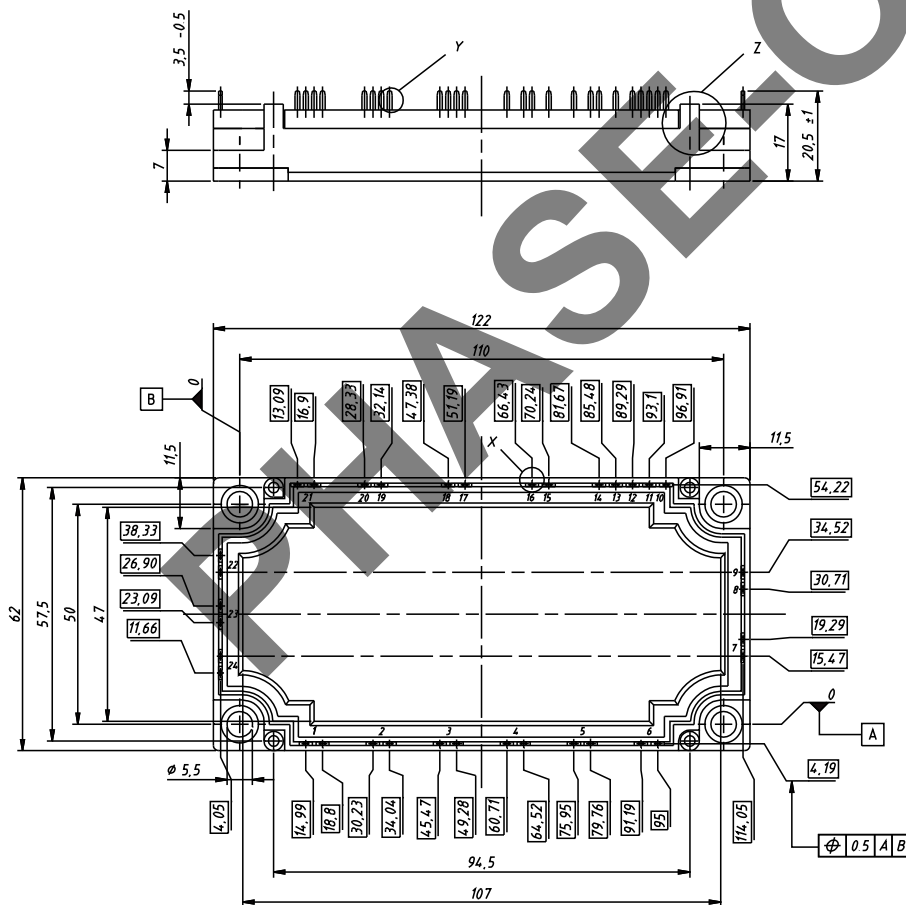
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$	$T = 25^{\circ}\text{C}$	4.75	5.0	5.25 k $\Omega$
$B_{25/50}$			3375	K

### Module

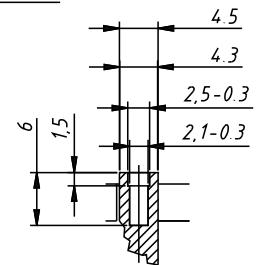
Symbol	Conditions	Maximum Ratings	
$T_{VJ}$	operating	-40...+125	$^{\circ}\text{C}$
$T_{JM}$		+150	$^{\circ}\text{C}$
$T_{stg}$		-40...+125	$^{\circ}\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
$M_d$	Mounting torque (M5)	3 - 6	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			5	m $\Omega$
$d_s$	Creepage distance on surface	6		mm
$d_A$	Strike distance in air	6		mm
$R_{thCH}$	with heatsink compound		0.01	K/W
Weight			300	g

Dimensions in mm (1 mm = 0.0394")



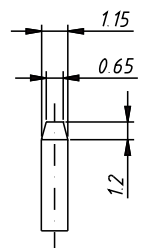
Detail Z



Detail X



Detail Y



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[25.640.5053.0](#)